PIEZOELECTRICITY Piezoelectric Coefficients

called the direct piezoelectric effect and was discovered by Jacques and Pierre Curie in 1880. Materials showing this phenomenon also conversely have a geometric strain proportional to an applied electric field. This is the converse piezo- where all quantities are tensors; *S* and *T* are second rank and electric effect. The root of the word "piezo" means "pressure"; **s** is fourth rank. Piezoelectricity creates additional strains by hence the original meaning of the word piezoelectricity im-
applied field **E**. The piezoele hence the original meaning of the word piezoelectricity implied ''pressure electricity'' (1,2).

Piezoelectric materials provide coupling between electrical $S_{ij} = S_{ijkl}T_{kl} + d_{ijk}$ and mechanical parameters. The material used earliest for its piezoelectric properties was single-crystal quartz. Quartz where *E* is the electric field and *d* is the piezoelectric constant crystal resonators for frequency control appear today at the which is the third rank tensor. This equation can be also ex-
heart of clocks and are also used in TVs and computers. Fer-
pressed in a matrix form such as given roelectric polycrystalline ceramics such as barium titanate ceramics: and lead zirconate titanate exhibit piezoelectricity when electrically poled. Since these ceramics possess significant and stable piezoelectric effects, that is, high electromechanical coupling, they are capable of producing large strains/forces and hence are extensively used as transducers. Piezoelectric polymers, notably polyvinyliden difluoride and its copolymers with trifluoroethylene and piezoelectric composites combining a piezoelectric ceramic with a passive polymer, have been developed which offer a high potential. Recently, thin films of piezoelectric materials are receiving attention due to their potential utilization in microsensors, microtransducers, and microactuators.

Piezoelectricity is being extensively utilized in the fabrication of various devices such as transducers, actuators, surface acoustic wave devices, frequency control, and so on. In this article we discuss the piezoelectric effect, a brief history of piezoelectricity followed by present-day piezoelectric materials
als that are used, and finally various potential applications of
piezoelectric field produced when a stress is applied
piezoelectric materials.
 $(E = gT)$. The

Relationship Between Crystal Symmetry and Properties

All crystals can be classified into 32 point groups according A measure of the effectiveness of the electromechanical ento their crystallographic symmetry. These point groups are ergy conversion is the electromechanical coupling factor *k* divided into two classes; one has a center of symmetry and which measures the fraction of the electrical energy converted another lacks it. There are 21 noncentrosymmetric point to mechanical energy when an electric field is applied or vice groups. Crystals belonging to 20 of these point groups exhibit versa when a material is stressed (5). The relationship is in

BIBLIOGRAPHY piezoelectricity. The cubic class 432, although lacking a center of symmetry, does not permit piezoelectricity. Of these 20 point groups, there are 10 polar crystal classes containing a unique axis, along which an electric dipole moment is oriented in the unstrained condition.

> Pyroelectric effect appears in any material that possesses a polar symmetry axis. As a result of this the material develops an electrical charge on the surface owing to change in magnitude of the dipole moment with changing temperature. Among the pyroelectric crystals whose spontaneous polarization are reorientable by application of an electrical field of sufficient magnitude (not exceeding the breakdown limit of the crystal) are ferroelectrics (3,4). Table 1 shows the crystallographic classification of the point groups.

Certain materials produce electrical charges on their surfaces
as a consequence of applied mechanical stress. The induced
charges are proportional to the mechanical stress. This is
 \overline{f} (force per unit area) causes a

$$
S = sT \tag{1}
$$

$$
\mathbf{S}_{ii} = \mathbf{S}_{ijkl} \mathbf{T}_{kl} + \mathbf{d}_{ijk} \mathbf{E}_{k} \tag{2}
$$

pressed in a matrix form such as given for the case in a poled

$$
\begin{bmatrix}\nS_1 \\
S_2 \\
S_3 \\
S_4 \\
S_5 \\
S_6\n\end{bmatrix} =\n\begin{bmatrix}\ns_{11} & s_{12} & s_{13} & & & & & & \\
s_{12} & s_{11} & s_{13} & & & & & \\
s_{13} & s_{13} & s_{33} & & & & \\
s_{14} & s_{44} & & & & & \\
s_{5} & 0 & s_{44} & & & & \\
s_{6}\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
T_2 \\
T_3 \\
T_4 \\
T_5 \\
T_6\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
T_2 \\
T_3 \\
T_4 \\
T_5 \\
T_6\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
T_2 \\
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T_4 \\
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T_6\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
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T_6\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
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T_6\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
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T_6\n\end{bmatrix}\n\begin{bmatrix}\nT_1 \\
T_2 \\
T_3 \\
T_4 \\
T_5 \\
T_6\n\end{bmatrix}\n\begin{bmatrix}\n0 & 0 & d_{31} \\
0 & 0 & d_{32} \\
0 & d_{15} & 0 \\
0 & 0 & 0\n\end{bmatrix}\n\begin{bmatrix}\nE_1 \\
E_2 \\
E_3\n\end{bmatrix}\n\begin{bmatrix}\nE_1 \\
E_2 \\
E_3\n\end{bmatrix}\n\begin{bmatrix}\n0 & 0 & 0 \\
0 & 0 & d_{33} \\
0 & 0 & 0 \\
0 & 0 & 0\n\end{bmatrix}
$$

THE PIEZOELECTRICITY the permittivity ϵ :

$$
g = d/\epsilon \tag{4}
$$

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		Crystal System										
Polarity	Symmetry	Cubic		Hexagonal		Tetragonal		Rhombo- hedral		Ortho- rhombic	Mono- clinic	Triclinic
Non-polar $[22]$	Centro $[11]$	m3m	m ₃	6/mmm	6/m	4/mmm	4/m	- 3m	$\overline{}$ 3	mmm	2/m	
	Non-centro [21]	432 — 43m	23	622 6m2	- 6	422 42m	$\overline{4}$	32		222		
Polar (Pyroelectric) $[10]$				6mm	6	4mm	4	3m	3	mm2	$\overline{2}$ m	

Table 1. Crystallographic Classification in Terms of Polarity and Centrosymmetry

Inside the bold line are piezoelectrics.

terms of k^2 .

$$
\mathbf{k}^2 = \frac{\text{Electrical energy converted to mechanical energy}}{\text{Input electrical energy}}
$$
 (5)

$$
\mathbf{k}^2 = \frac{\text{Mechanical energy converted to electrical energy}}{\text{Input mechanical energy}} \quad (6)
$$

$$
\mathbf{k}^2 = \mathbf{d}^2/(\epsilon \cdot \mathbf{s})\tag{7}
$$

k is always less than 1, because k^2 is below 1. Typical values
of *k* are 0.10 for quartz, 0.4 for BaTiO₃ ceramic, 0.5 to 0.7 for
PZT (lead zirconate-titanate) ceramic and 0.1 to 0.3 for PVDF There is another class

$$
Q_m = 2\pi \times \frac{\text{Energy stored over one cycle}}{\text{Energy dissipated per cycle}} \tag{8}
$$

As stated already the discovery of piezoelectricity in quartz

(which is not ferroelectric) was done by Pierre and Jacques

Curie in 1880. Ferroelectricity can provide the creation of use-

ful piezoelectric materials. Roc electric discovered in 1921. Until 1940 only two types of ferroelectrics were known, Rochelle salt and potassium dihydrogen **PIEZOELECTRIC MATERIALS** phosphate and its isomorph. From 1940 to 1943, unusual dielectric properties such as the abnormally high dielectric con-
stant of barium titanate BaTiO₃ were discovered indepen-
dently by Wainer and Salmon, Ogawa, and Wul and Golman.
After the discovery, compositional modific ramics were becoming well established in a number of device **Single Crystals** applications.

In the 1950s Jaffe and co-workers established the lead zir- More recently, the piezoelectric ceramics are widely used for

. morphotropic phase boundary, that is, the composition-dependent and temperature independent rhombohedral-tetragonal phase change. Since then, the PZT system with various additives has become the dominant piezoelectric ceramics for potential applications. Other ferroelectric perovskite compounds or were also extensively examined. The discovery of PZT solid solution systems was rapidly followed by its exploitation in a number of practical piezoelectric applications.

Kawai et al. discovered in 1969 that certain polymers, notably polyvinyliden difluoride, are piezoelectric when which also can be expressed by stretched during fabrication. Such piezoelectric polymers are also useful for some transducer applications. In 1978 Newnham et al. improved composite piezoelectric materials by com-

PZT (lead zirconate-titanate) ceramic and 0.1 to 0.3 for PVDF
(polyvinylidene difluoride) polymer. Another important mate-
rial parameter is the mechanical quality factor Q_m which de-
termines the frequency characterist in piezoelectric actuator field. Recent breakthrough in the growth of high quality large single crystal relaxor piezoelectric compositions has brought the interest in these materials for wide applications ranging from high strain actuators to HISTORY OF PIEZOELECTRICITY **HISTORY OF PIEZOELECTRICITY** bigh frequency transducers for the medical ultrasound de-
vices due to their superior electromechanical characteristics.

conate–lead titanate system (called PZT system) as suitable a large number of applications. However, single crystal matefor inducing strong piezoelectric effects. The maximum piezo- rials retain their utility, being essential for application fields electric response was found for PZT compositions near the such as frequency stabilized oscillators and surface acoustic

Parameter	Quartz	BaTiO ₃	PZT 4	PZT 5H	(Pb, Sm)TiO ₃	PVDF-TrFE
d_{33} (pC/N)	2.3	190	289	593	65	33
$g_{33}\ (10^{-3}\mathrm{Vm/N})$	57.8	12.6	26.1	19.7	42	380
$k_{\rm t}$	0.09	0.38	0.51	0.50	0.50	0.30
$k_{\rm p}$		0.33	0.58	0.65	0.03	
$\epsilon_{33}^{T}/\epsilon_0$	5	1700	1300	3400	175	6
$Q_{\rm m}$	$>10^{5}$		500	65	900	$3 - 10$
T_c ^o C)		120	328	193	355	

Table 2. Properties of Piezoelectric Materials

devices. The most popular single-crystal piezoelectric materi- structure consists of a simple cubic unit cell with a large catals are quartz, lithium niobate (LiNbO₃) and lithium tanta- ion A on the corner, a smaller cation B in the body center, late (LiTaO₃). The single crystals are anisotropic, which gives and oxygen O in the centers of the faces. The structure is different material properties depending on the cut of the ma- a network of corner-linked oxygen

Quartz is a well-known piezoelectric material. α -quartz belongs to triclinic crystal system with point group 32 and has incorporating various cations in the perovskite structure. a phase transition at 537° C to β -type which is not a piezoelectric. Quartz has the cut with a zero temperature coefficient. **Barium Titanate.** Barium titanate (BaTiO₃) is one of the For instance, quartz oscillators using a thickness shear mode most thoroughly studied and most widel

rection is along the c-axis. These materials have high electro-
mechanical coupling coefficients for surface acoustic waves. In points in the [001] direction (tetragonal phase), below 5°C it
addition large single crystals addition, large single crystals can easily be obtained from
their melt using the conventional Czochralski technique. in the [111] (orthrhombic phase) and below -90° C
Thus both materials occupy very important position Thus, both materials occupy very important positions in the

Perovskite Structure. Most of the piezoelectric ceramics used as commercial piezoelectric materials. have perovskite structure ABO₃, as shown in Fig. 1. This ideal **Lead Zirconate–Lead Titanate.** Piezoelectric Pb(Zr,Ti)O₃

of a simple cubic unit cell with a large cation A on the corner, a smaller cation B in the body center, and oxygen O in the centers of boundary. This enhancement in piezoelectric effect is attribthe faces. uted to the increased ease of reorientation of the polarization

a network of corner-linked oxygen octahedra surrounding B terials and the direction of bulk or surface wave propagation. cations. Piezoelectric properties of perovskite-structure materials can be easily tailored depending on their applications by

For instance, quartz oscillators using a thickness shear mode
of AT-cut are extensively used for clock sources in computers,
of AT-cut are extensively used for clock sources in computers,
and frequency stabilized ones in chanical quality factor $Q_m > 10^5$.

Lithium niobate and lithium tantalate belong to an isomor-

phous crystal system and are composed of oxygen octahedron.

The Curie point the crystal becomes polar and

moments. At the surface acoustic wave device application field. fected by its own stoichiometry, microstructure, and by dopants entering into the A or B site solid solution. Modified **Ceramics Ceramics** ceramic BaTiO₃ with dopants such as Pb or Ca ions have been

solid solutions (PZT) ceramics have been widely used because of their superior piezoelectric properties. The phase diagram of the PZT system $(PbZr_xTi_{1-x}O₃)$ is shown in Fig. 3. The crystalline symmetry of this solid-solution system is determined by the Zr content. Lead titanate also has a tetragonal ferroelectric phase of perovskite structure. With increasing Zr content, *x*, tetragonal distortion decreases and when $x > 0.52$ the structure changes from tetragonal 4 mm phase to another ferroelectric phase of rhombohedral 3 m symmetry. This transition is rather independent of temperature. The line dividing the two phases is called morphotropic phase boundary, that is, the change of symmetry occurs only as a function of composition. This composition is considered to have both phases. Figure 4 shows the dependence of several *d* constants on com-**Figure 1.** Perovskite structure ABO₃. This ideal structure consists position near the morphotropic phase boundary. The *d* con-
of a simple cubic unit cell with a large cation A on the corner a stants have their highe

Figure 2. Dielectric constants of BaTiO₃ as a function of temperature. Three anomalies accompanied with phase transitions can be observed.

acceptors changes the properties dramatically. Donor doping spectively. (Pb, Nd)(Ti, Mn, In)O₃ ceramics with a zero tem-
with ions such as Nb^{5+} or Ta⁵⁺ provides soft PZTs like PZT-5, perature coefficient of surface with ions such as Nb^{5+} or Ta⁵⁺ provides soft PZTs like PZT-5, because of the facility of a domain motion due to the resulting developed as a superior substrate materials for SAW device Pb-vacancy. On the other hand, acceptor doping such as $Fe³⁺$ applications (10). or Sc^{3+} leads to hard PZTs such as PZT-8, because oxygen vacancies will pin the domain wall motion. **Polymers**

be obtained easily, because they break up into a powder when cooled through the Curie temperature. This is due to the large. pling, that is, large k/k_p ratio. Here, k_t and k_p are thickness- polymerization of vinilydene difluoride with trifluoroethylene

try of this solid-solution system is determined by the Zr content. The boundary. line dividing the two, tetragonal and rhombohedral phases is called morphotropic phase boundary.

under electric field. Doping the PZT material with donors or extensional and planar electromechanical coupling factors, re-

Lead Titanate. Lead titanate has a large crystal distortion. Polyvinylidene difluoride, PVDF or PVF2, is piezoelectric
TiO_s has tetragonal structure at room temperature with its when stretched during fabrication. Thin sh $PbTiO₃$ has tetragonal structure at room temperature with its when stretched during fabrication. Thin sheets of the cast tetragonality approximately equal to 1.063. The Curie tem-
polymer are then drawn, stretched, tetragonality approximately equal to 1.063. The Curie tem- polymer are then drawn, stretched, in the plane of the sheet perature is 490°C. Densely sintered PbTiO₃ ceramics cannot in at least one direction, and frequentl perature is 490°C. Densely sintered $PbTiO_3$ ceramics cannot in at least one direction, and frequently also in the perpendic-
be obtained easily, because they break up into a powder when ular direction, to make the materi polar phase. Crystallization from melt forms nonpolar α spontaneous strain which occurs at the transition. Lead ti-
phase, which can be converted into another polar β -phase by tanate ceramics modified by adding small amounts of addi- a uniaxial or biaxial drawing operation; these dipoles are then tives exhibit a high piezoelectric anisotropy. Either (Pb, reoriented through electric poling. Large sheets can be manu- $Sm)TiO₃(8)$ or (Pb, Ca)TiO₃ (9) has extremely low planar cou- factured and thermally formed into complex shapes. The co-

Figure 4. Several piezoelectric *d* strain coefficients versus composition near the morphotropic phase boundary for the PZT system. The **Figure 3.** Phase diagram of the PZT system. The crystalline symme- *d* coefficients have their highest values near the morphotropic phase

(TrFE) results in random copolymer (PVDF-TrFE) with a sta- tion in actuators. This relaxor ferroelectrics can also provide ble, polar β -phase. This polymer need not be stretched; it can an induced piezoelectric effect. That is, the electromechanical be poled directly as formed. The thickness-mode coupling co- coupling factor k_t varies with the applied dc bias field. As the efficient of 0.30 has been reported. Such piezoelectric poly- dc bias field increases, the coupling increases and saturates. mers are used for directional microphones and ultrasonic hy- This behavior is reproducible. These materials would be ap-

Piezocomposites composed of a piezoelectric ceramic and poly-
mer are promising materials because of excellent and tailored
of $Ph(M\sigma_{\nu}Nh_{\nu})O_{\nu}(PNN)$ $Ph(Zn_{\nu}Nh_{\nu})O_{\nu}(PXN)$ and hinary mer are promising materials because of excellent and tailored of $Pb(Mg_{1/3}Nb_{2/3})O_3$ (PMN), $Pb(Zn_{1/3}Nb_{2/3})O_3$ (PZN) and binary properties. The geometry for two-phase composites can be systems of these materials combin properties. The geometry for two-phase composites can be systems of these materials combined with PbTiO₃ (PMN–PT classified according to the connectivity of each phase $(1, 2, or$ and PZN–PT) exhibit extremely large elect classified according to the connectivity of each phase $(1, 2, \text{or} \cdot \text{and } PZN-PT)$ exhibit extremely large electromechanical cou-
3 dimensionally) into 10 structures; 0-0, 0-1, 0-2, 0-3, 1-1, 1-2, pling factors (14.15) . L 1-3, 2-2, 2-3 and 3-3 (11). A 1-3 piezocomposite, or PZT–rod/ ezoelectric constants have been found for these solid-solution polymer–matrix composite, is identified as a most promising crystals with morphotropic phase boundary compositions.
candidate. The advantages of this composite are high coupling PZN-8%PT single crystals were found to poss candidate. The advantages of this composite are high coupling PZN-8%PT single crystals were found to possess high k_{33}
factors, low acoustic impedance, good matching to water or value of 0.94 for (001) crystal cuts. The human tissue, mechanical flexibility, broad bandwidth in ventional PZT ceramics is usually 0.70 to 0.80. combination with low mechanical quality factor, and the pos- More recently, it was reported that these relaxor based fersibility of making undiced arrays by only structuring the elec- roelectric single crystals also exhibit ultrahigh strain levels trodes. The thickness-mode electromechanical coupling of the not available with current piezoelectric ceramics (16). Pseucomposite can exceed the k_t (0.40 to 0.50) of the constituent docubic $\langle 001 \rangle$ oriented relaxor based rhombohedral crystal
ceramic almost approaching the value of the rod-mode elec-
such as $(1 - x)PZN - xPT$ ($x < 0.09$) an ceramic, almost approaching the value of the rod-mode elec- such as $(1 - x)PZN - xPT$ $(x < 0.09)$ and $(1 - x)PMN -$
tromechanical coupling $k_{\infty}(0.70 \text{ to } 0.80)$ of that ceramic (12) $xPT (x < 0.35)$ were reported to have **E**-field tromechanical coupling, k_{33} (0.70 to 0.80) of that ceramic (12). $xPT(x < 0.35)$ were reported to have *E*-field induced strains 3
Acoustic impedance is the square root of the product of its up to 0.6% with negligible hy Acoustic impedance is the square root of the product of its up to 0.6% with negligible hysteresis. Ultrahigh strain levels density and elastic stiffness. The acoustic match to tissue or more than 1.5%, nearly an order density and elastic stiffness. The acoustic match to tissue or more than 1.5%, nearly an order of magnitude higher than water (1.5 Mrayls or kgm⁻²s⁻¹) of the typical niezoceramics polycrystalline PZTs or electrostrict water (1.5 Mrayls or kgm⁻²s⁻¹) of the typical piezoceramics (20 to 30 Mrayls) is significantly improved by forming a com-
posite structure, that is, by replacing heavy and stiff ceramic mation. by light and soft polymer. Piezoelectric composite materials are especially useful for underwater sonar and medical diag- **APPLICATIONS OF PIEZOELECTRIC MATERIALS** nostic ultrasonic transducer applications.

binary compounds with a Wurtzite-type structure, which can generation of charge at high voltage such as for the spark be sputter-deposited in a *c*-axis oriented thin film on a variety ignition of gas in space heaters, cooking stoves, and cigarette of substrates. ZnO has large piezoelectric coupling and its lighters. Using the converse effect, mechanical small displacethin films are widely used in bulk acoustic and surface acous- ments and vibrations can be produced for actuators by tic wave devices. The fabrication of highly c-axis oriented ZnO applying a field. Acoustic and ultrasonic vibrations can be films has been extensively studied and developed. The perfor- generated by an alternating field tu films has been extensively studied and developed. The perfor- generated by an alternating field tuned at the mechanical res-
mance of ZnO devices is, however, limited due to their small onance frequency of a piezoelectric mance of ZnO devices is, however, limited due to their small onance frequency of a piezoelectric device, and can be de-
piezoelectric coupling (20 to 30%). PZT thin films are expected tected by amplifying the field generat piezoelectric coupling (20 to 30%). PZT thin films are expected tected by amplifying the field generated by vibration incident
to exhibit higher piezoelectric properties. At present, the on the material, which is usually u to exhibit higher piezoelectric properties. At present, the on the material, which is usually used for ultrasonic trans-
growth of PZT thin film is being carried out for use in micro- ducers. The other important applicatio growth of PZT thin film is being carried out for use in microity include the control of frequency. The application of piezo- transducers and microactuators.

terms of having broad phase transition from paraelectric to voltage applications; gas ignitors, ultrasonic cleaning, and ferroelectric state, strong frequency dependence of dielectric machining. Piezoelectric-based sensors, for instance, accelerconstant (i.e., dielectric relaxation) and weak remanent polar- ometers, automobile knock sensors, vibration sensors, strain ization. Lead based relaxor materials have complex disor- gages, and flow meters have been developed, because pres- B_2) O_3 ($B_1 = Mg^{2+}$, Zn^{2+} , Sc^{3+} , $B_2 = Nb^{5+}$, Ta^{5+} , W^{6+}). The B site through piezoelectric effect. Examples are distributed randomly in the crystal. The charac- are given in the following sections. cations are distributed randomly in the crystal. The characteristic of relaxors is a broad and frequency dispersive dielec- **Ultrasonic Transducers** tric maximum. Relaxor-type electrostrictive materials such as lead magnesium niobate $Pb(Mg_{1/3}Nb_{2/3})O_3$ -lead titanate One of the most important applications of piezoelectric mate-PbTiO₃ solid solution (PMN–PT) are very suitable for applica- rials is based on ultrasonic echo field (17,18). Ultrasonic

drophones. **plied for ultrasonic transducers which can be tunable by the** bias field (13).

Recently, single-crystal relaxor ferroelectrics have been de- **Composites** veloped which show great promising results in ultrasonic pling factors (14.15) . Large coupling coefficients and large pivalue of 0.94 for (001) crystal cuts. The k_{33} value of the con-

 $docubic \langle 001 \rangle$ oriented relaxor based rhombohedral crystals

Piezoelectric materials can provide coupling between electri-Thin-Films
cal and mechanical energy and thus have been extensively
Both zinc oxide (ZnO) and aluminum nitride (AlN) are simple
The direct piezoelectric effect is most obviously used in the The direct piezoelectric effect is most obviously used in the electric materials ranges over many technology fields including ultrasonic transducers, actuators and ultrasonic **Relaxor-Type Ferroelectric Materials** motors, electronic components such as resonators, wave fil-Relaxor ferroelectrics differ from normal ferroelectrics in ters, delay lines, SAW devices and transformers, and high dered perovskite structures with a general formula Pb(B₁, sure and vibration can be directly sensed as electric signals B_0) O_0 (B₁ = Mo²⁺ Zn²⁺ Sc³⁺ B₂ = Nb⁵⁺ T₂⁵⁺ W⁶⁺) The B site through piezoelec

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transducers convert electrical energy into mechanical form when generating an acoustic pulse and convert mechanical energy into an electrical signal when detecting its echo. Currently, piezoelectric transducers are being used in medical ultrasound for clinical applications ranging from diagnosis to therapy and surgery. They are also used for underwater detection, such as sonar and fish finding, and nondestructive testing.

The ultrasonic transducers often operate in a pulse-echo mode. The transducer converts electrical input into acoustic wave output. The transmitted waves propagate into a body and echoes are generated which travel back to be received by the same transducer. These echoes vary in intensity according to the type of tissue or body structure, thereby creating images. An ultrasonic image represents the mechanical properties of the tissue, such as density and elasticity. We can recognize anatomical structures in an ultrasonic image since the organ boundaries and fluid-to-tissue interfaces are easily dis-
cerned. The ultrasonic imaging process can also be done in
real time. This means we can follow rapidly moving struc-
real time. This means we can follow rapid tures such as the heart without motion distortion. In addition,

There are various types of transducers used in ultrasonic \overline{t} to the efficiency of converting electric energy into a
coustic and integrigy. Mechanical sector transducers consist of single, rela-
integrigy. Here is in

electric material and backing (19). One or more matching layers are used to increase sound transmissions into tissues. The backing is added to the rear of the transducer in order to damp the acoustic backwave and to reduce the pulse duration. Piezoelectric materials are used to generate and detect ultrasound. In general, broadband transducers should be used for medical ultrasonic imaging. The broad bandwidth response corresponds to a short pulse length, resulting in better axial resolution. Three factors are important in designing broad bandwidth transducers. The first is acoustic impedance matching, that is, effectively coupling acoustic energy to the

ultrasound is one of the safest diagnostic imaging techniques.

It does not use ionizing radiation like x rays and thus is routinely used for fetal and obstetrical imaging. Useful areas for

ultrasonic imaging include car

phased array transducer the acoustic beam is steered by sig-
nals than the planar coupling factor k_p is much less
nals that are applied to the elements with delays, creating a
setor display. This transducer is useful fo sector display. This transducer is useful for cardiology appli-
cations where positioning between the ribs is necessary.
Figure 5 shows the basic ultrasonic transducer geometry.
The transducer is mainly composed of matchin

Table 3. Comparison of Ultrasonic Transducer Materials

	PZT Ceramic	PVDF Polymer	PZT-Polymer Composite	ZnO Film
$k_{\scriptscriptstyle{\text{t}}}$	$0.45 - 0.55$	$0.20 - 0.30$	$0.60 - 0.75$	$0.20 - 0.30$
Z (Mrayls)	$20 - 30$	$1.5 - 4$	$4 - 20$	35
$\epsilon_{33}^{T}/\epsilon_0$	200-5000	10	$50 - 2500$	10
$tan \delta$ (%)	$<$ 1	$1.5 - 5$	$<$ 1	$<$ 1
$Q_{\rm m}$	$10 - 1000$	$5 - 10$	$2 - 50$	10
ρ (g/cm ³)	$5.5 - 8$	$1 - 2$	$2 - 5$	$3 - 6$

tage to PZT and other lead based ceramics is their large uses a mechanical shell, generally made of metal such as steel acoustic impedance (approximately 30 Mrayls) compared to or brass, to convert hydrostatic stress to a stress along one or body tissue (1.5 Mrayls). Single or multiple matching layers more of the sensitive axes of a stack of piezoelectric ceramic with intermediate impedances needed to be used in the case plates or rings (24). The flextensional transducers with differ-

On the other hand, piezoelectric polymers, such as polyvi- an extremely high sensitivity. nyliden-difluoride-trifluoroethylene, have much lower acoustic impedance (4 to 5 Mrayls) than the ceramics and thus
provide better matching with soft tissues. However, piezopo-**Actuators and Motors**

the depth to less than 1 cm. Higher-frequency transducers (10 traordinarily large apparent electrostriction though it is a
MHz to 50 MHz) are used for endoscope-based imaging and secondary phenomenon of the electromechanic for catheter-based intravascular imaging. At higher frequen-
ciss over 100 MHz applications are used in the field of ultra-
temperature in 0.9PMN-0.1PT (26). The magnitude of the cies over 100 MHz applications are used in the field of ultra-
sound microscopy. The operating frequency of the transducer electrostriction is 10^{-3} and this material has almost no hys-
sound microscopy. The operating f sound microscopy. The operating frequency of the transducer electros
is directly related to the thickness and velocity of sound in teresis. is directly related to the thickness and velocity of sound in the piezoelectric materials employed. As frequency increases resonator thickness decreases. For a 3.5 MHz transducer, PZT ceramic thickness needs to be roughly 0.4 mm. Most conventional ceramic transducers, such as PZT, are limited to frequencies below nearly 80 MHz because of the difficulty of fabricating thinner devices (21). For microscopic applications at frequencies over 100 MHz, corresponding to the thickness of less than 20 μ m, piezoelectric thin-film transducers such as ZnO have to be used (22).

The design of ultrasonic transducers with piezoelectrics used in medical field was mentioned above. Another major ultrasonic transducer application is the underwater sonar transducer employed as both acoustic source and hydrophone. Sonar (sound navigation and ranging) is used to explore the ocean and underwater objects. Hydrophones are underwater microphones for detecting sound in water and under hydrostatic pressure. The representative transducers widely used for high-power and low-frequency active sonar include the Tonpilz and flextensional structures. The design of the Tonpilz transducer typically involves head and tail masses which are configured for impedance matching and a central piezoceramic section, whose shape roughly resembles a mushroom (23). This transducer is made from stacks of rings electroded on the flat surfaces and electrically connected in parallel and **Figure 6.** Longitudinal induced strain curve at room temperature in are electrically insulated for each other held together with a 0.9 PMN–0.1PT as a function of electric field. The magnitude of the stress rod. On the other hand, the flextensional transducer electrostriction is 10^{-3} a stress rod. On the other hand, the flextensional transducer

of PZT to improve acoustic matching. ent shapes of the outer shell have been designed to achieve

ly
mers are leas sensitive than the ceramics and they have
relatively low dielective constants, requiring large drive volt-
are defined as translates axist in ectance age and giving poor noise performance due to electrica

tative types: multilayer, bimorph, and moonie types. generative force (100 N) with quicker response (100 μ s) than

tors. Simple devices composed of a disk and multilayer type The piezoelectric impact dot-matrix printer is the first mass-
directly use the strain induced in a ceramic by the applied produced device using multilayer cerami directly use the strain induced in a ceramic by the applied produced device using multilayer ceramic actuators. The ad-
electric field. Complex devices do not use the induced strain vantage of the piezoelectric printer hea electric field. Complex devices do not use the induced strain vantage of the piezoelectric printer head compared to the con-
directly but use the magnified displacement through a special ventional magnetic types are: low e directly but use the magnified displacement through a special ventional magnetic types are: low energy consumption, low magnification mechanism such as unimorph, bimorph, and heat generation, and fast printing speed. The l magnification mechanism such as unimorph, bimorph, and heat generation, and fast printing speed. The longitudinal
moonie. The most popularly used multilayer and bimorph multilayer actuators do not exhibit a large displacem moonie. The most popularly used multilayer and bimorph multilayer actuators do not exhibit a large displacement and
types have the following characteristics: The multilayer type thus a suitable displacement magnification m types have the following characteristics: The multilayer type thus a suitable displacement magnification mechanism is nec-
does not show a large displacement (10 μ m), but has advan-
essary. The displacement induced in does not show a large displacement (10 μ m), but has advan- essary. The displacement induced in a multilayer actuator tages in generation force (1000 N), response speed (10 μ s), mushes un the force point and its disp tages in generation force (1000 N), response speed (10 μ s), pushes up the force point, and its displacement magnification lifetime (10¹¹ cycles), and the electromechanical coupling fac-
is carried out through hinge l lifetime (10¹¹ cycles), and the electromechanical coupling fac-
tor k_{33} (0.70). The bimorph type exhibits a large displacement wire stroke. When the displacement in the niezoactuator is 8 (300 μ m), but shows disadvantages in generation force (1 N), response speed (1 ms) , lifetime (10^8 cycles) and the electromechanical coupling factor k_{eff} (0.10). For instance, in a 0.65 PMN–0.35 PT multilayer actuator with 99 layers of 100 μ m thick sheets $(2 \times 3 \times 10 \text{ mm}^3)$, an 8.7 μ m displacement is generated by a 100 V voltage, accompanied by a slight hysteresis. The transmit response of the induced displacement after the application of a rectangular voltage is as quick as $10 \mu s$. In conclusion, the multilayer exhibits the field induced strain of 0.1% along the length.

Unimorph and bimorph devices are defined by the number of piezoelectric ceramic plates: only one ceramic plate is bonded onto an elastic shim, or two ceramic plates are bonded bonded onto an elastic shim, or two ceramic plates are bonded
together simultaneously. The bimorph causes bending deformation because each piezoelectric plate bonded together pro- **Figure 8.** Two types of piezoelectric bimorphs: (a) antiparallel polarduces extension or contraction under an electric field. In gen- ization type and (b) parallel polarization type.

eral, there are two types of piezoelectric bimorph: antiparallel polarization type and parallel polarization type, as shown in Fig. 8. Two poled piezoelectric plates with *t*/2 in thickness and *L* in length are bonded with their polarization directions opposite or parallel to each other. In cantilever bimorph configuration whose one end is clamped, the tip displacement δ_z under an applied voltage *V* is provided as follows

$$
\delta_z = 3/2 \cdot d_{31} (L^2/t^2) V \quad \text{(antiparallel type)} \tag{9}
$$

$$
\delta_z = 3d_{31}(L^2/t^2)V \qquad \text{(parallel type)} \tag{10}
$$

The resonance frequency f_r for both types is given by

$$
f_r = 0.16t/L^2 \left(\rho S_{11}^E\right)^{-1/2} \tag{11}
$$

where ρ is density and S_{11}^{E} is elastic compliance. A metallic sheet (called a shim) is occasionally sandwiched between the two piezoelectric plates to increase the reliability, that is, the structure can be maintained even if the ceramics fracture. Using the bimorph structure, a large magnification of the displacement is easily obtainable. However, the disadvantages include a low response speed (1 kHz) and low generative force.

A composite actuator structure called moonie has been developed to amplify the small displacements induced in a piezoelectric ceramic. The moonie consists of a thin multilayer element and two metal plates with a narrow moon-shaped cavity bonded together. This device has intermediate characteristics between the conventional multilayer and bimorph ac tuators; this shows an order of magnitude larger displace-**Figure 7.** Structures of ceramic actuators. There are three represen- ment $(100 \mu m)$ than the multilayer, and much larger the bimorph.

Some examples of applications of piezoelectric and elec-Figure 7 shows the design classification of ceramic actua-
trostrictive actuators mentioned already are described next.
tors. Simple devices composed of a disk and multilayer type The piezoelectric impact dot-matrix printe wire stroke. When the displacement in the piezoactuator is 8

 μ m, the wire stroke of 240 μ m can be obtained, that is the magnification rate is 30 times.

Bimorph structures are commonly used for VCR head tracking actuators, because of their large displacements. An autotracking scan system uses the piezoelectric actuators so that the head follows the recording track even while driven at both still and quick modes. As can be anticipated, the bimorph drive is inevitably accompanied by a torsional motion. To obtain a perfect parallel motion a special mechanism has at both still and quick modes. As can be anticipated, the bi-
morph drive is inevitably accompanied by a torsional motion.
To obtain a perfect parallel motion a special mechanism has
to be employed. Piezoelectric bimorphs phonograph pick-up cartridges, and cantilever bimorphs with **Figure 9.** Vibratory coupler type ultrasonic motor. A vibratory piece or motors a single entry piece or promotors. Piezeologized pumps for gas or liquid utilizing ap is attached to a rotor or a slider with a slight cant a erometers. Piezoelectric pumps for gas or liquid utilizing an alternating bending motion of bimorph have been developed

electronically controlled shock absorber has both controllabil- **Resonators and Filters** ity and comfortablility simultaneously.

piezoelectric actuators using a resonant vibration. In ultra- resulting in the fall of impedance. This phenomenon enables sonic motors linear motion is obtained from the elliptical vi-
bration through frictional force. The motor basically consists required to pass a certain selected frequency band or to stop of a high-frequency power supply, a vibrator, and a slider. a given band. The bandwidth of a filter fabricated from a pi-The vibrator is composed of a piezoelectric driving component ezoelectric material is determined by the square of the couand an elastic vibrator part, and the slider is composed of an elastic moving part and a friction coat. The characteristics of the ultrasonic motors are low speed and high torque compared to the conventional electromagnetic motors with high speed and low torque (25,27).

The ultrasonic motors are classified into two types: a standing-wave type and a propagating-wave type. The standing wave is expressed by

$$
V(s(x, t) = A\cos(kx) \cdot \cos(\omega t) \tag{12}
$$

while the propagation wave is given by

$$
Vp(x, t) = A \cos(kx - \omega t)
$$

= $A \cos(kx) \cdot \cos(\omega t) + A \cos(kx - \pi/2) \cdot \cos(\omega t - \pi/2)$

for intravenous drip in
piecinon in hospitals and for medication and diabetes. Pi-A propagating wave can be generated by superimposing two
dispensers in chemotherapy, chronic pain, and diabetes. Pi-A propagating wave can

When a piezoelectric body vibrates at its resonant frequency **Ultrasonic Motors.** An ultrasonic motor is an example of it absorbs considerably more energy than at other frequencies required to pass a certain selected frequency band or to stop pling coefficient k, that is, nearly proportional to k^2 . Quartz

Figure 10. Principle of the propagating wave type ultrasonic motor. A surface particle of the elastic body draws an elliptic locus due to (13) the coupling of longitudinal and transverse waves.

crystals with very low *k* value of about 0.1 can pass very narrow frequency bands of approximate 1% of the center resonance frequency. On the other hand, PZT ceramics with a planar coupling coefficient of about 0.5 can easily pass a band of 10% of the center resonance frequency. The sharpness of the passband is dependent on the mechanical quality factor Q_{m} of the materials. Quartz has also a very high Q_m of about 10^6 which results in a sharp cut-off to the passband and well-
defined frequency of the oscillator.

with a center frequency ranging from 200 kHz to 1 MHz and acoustic energy back to an electrical signal. with a bandwidth of several percent of the center frequency. For a frequency of 455 kHz the disk diameter needs to be about 5.6 mm. However, if the required frequency is higher
the short and long delays are achievable on reasonable size
than 10 MHz, other modes of vibration such as the thickness
extensional mode are exploited, because of

wave can be electroacoustically accessed and tapped at the substrate surface and its velocity is approximately 10^4 times slower than an electromagnetic wave. The SAW wavelength is on the same order of magnitude as line dimensions which V_s is the SAW velocity and f_0 is the center frequency of the can be photolithographically produced and the lengths for device. SAW velocity is an important p

that coupling between two parts will only be efficient at resonance. wave passes across a surface coated with a thin massless con-

defined requency of the oscillator.

A simple resonator is a thin disk type, electroded on its

plane faces and vibrating radially for applications in filters

plane faces and vibrating radially for applications in filters

energy filter. In this structure the top electrode is split so
that coupling between the two parts will only be efficient at
resonance. More stable filters suitable for telecommunication
systems have been made from single (TCD), electromechanical coupling factor, and propagation **SAW Devices** loss. Surface acoustic waves can be generated and detected by A surface acoustic wave (SAW) also called a Rayleigh wave is
composed of a coupling between longitudinal and shear waves
in which the SAW energy is confined near the surface. An
associated electrostatic wave exists for a tric substrate, which allows electroacoustic coupling via a surface wave. If an KF source with a frequency, f , is applied transducer. The advantages of SAW technology are that the to the electrode having periodicity, d

$$
f = f_0 = V_s/d \tag{14}
$$

the center frequency. Another important parameter for many applications is temperature sensitivity. For example, the temperature stability of the center frequency of SAW bandpass filters is a direct function of temperature coefficient for the velocity and delay for the material used. The first-order temperature coefficient of delay is given by

$$
(1/\tau) \cdot (d\tau/dT) = (1/L) \cdot (dL/dT) - (1/V_{\rm s}) \cdot (dV_{\rm s}/dT) \quad (15)
$$

where $\tau = L/V_s$ is the delay time and *L* is the SAW propaga-Top Bottom $\frac{1}{2}$ Bottom tion length. The surface wave coupling factor, k_s^2 , is defined in **Figure 11.** Trapped-energy type filter. The top electrode is split so terms of the change in SAW velocity which occurs when the

Table 4. SAW Material Properties

	Material	Cut-Propagation Direction	k^2 (%)	TCD (ppm/C)	V_0 (m/s)	ϵ_{r}
	Quartz	$ST-X$	0.16	$\mathbf{0}$	3158	4.5
	LiNbO ₃	$128^{\circ}Y - X$	5.5	-74	3960	35
Single crystal	LiTaO ₃	$X112^\circ - Y$	0.75	-18	3290	42
	$Li_2B_4O_7$	$(110)-\langle001\rangle$	0.8	$\mathbf{0}$	3467	9.5
	$PZT-In(Li_{3/5}W_{2/5})O_3$		1.0	10	2270	690
Ceramic	(Pb, Nd)(Ti, Mn, In)O ₃		2.6	$<$ 1	2554	225
	ZnO/glass		0.64	-15	3150	8.5
Thin film	ZnO/Sapphire		1.0	-30	5000	8.5

ductor, so that the piezoelectric field associated with the wave input transducer converts the electrical signal to a shear is effectively shorted-circuited. The coupling factor, k_s^2 , is ex-

$$
k_s^2 = 2(V_f - V_m)/V_f
$$
 (16)

where V_f is the free surface wave velocity, and V_m the velocity corders. on the metallized surface. In actual SAW applications, the value of $k_{\rm s}^2$ relates to the maximum bandwidth obtainable and **Piezoelectric Transformer**

or K_2O doped SiO_2 glass in which the velocity of sound is and output parts. nearly independent of temperature. PZT ceramic transducers are soldered on two metallized edges of the slice of glass. The **BIBLIOGRAPHY**

Figure 13. Fundamental Rosen-type structure of piezoelectric trans- *electric Materials,* Oxford: Clarendon Press, 1977. former. Two differently-poled parts coexist in one piezoelectric plate. 5. *IEEE Standard on Piezoelectricity,* New York: IEEE, Inc., 1978.

acoustic wave which travels through the slice. At the output pressed by transducer the wave is reconverted into an electrical signal delayed by the length of time taken to travel around the slice. Such delay lines are used in color TV sets to introduce a delay of approximately 64 μ s and are also employed in videotape re-

the amount of signal loss between input and output, de-
thermining the fractional bandwidth versus minimum inser-
thermining the fractional bandwidth versus minimum inser-
thermining the fractional bandwidth versus minimu **Delay Lines Delay Lines** are formed at the side surface of the rectangular plate. This are formed at the side surface of the rectangular plate. This A delay line can be formed from a slice of glass such as PbO transformer uses piezoelectric transverse mode for the input

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PIEZOELECTRIC OSCILLATIONS. See SPACE CHARGE. PIEZOELECTRICS. See PIEZOELECTRICITY. **PIEZOELECTRIC SURFACE ACOUSTIC WAVE DE-VICES.** See SURFACE ACOUSTIC WAVE DEVICES.

PIEZOELECTRIC THIN FILMS. See THIN FILMS.